

ABSTRACT

WORKPIECE EVALUATING METHOD

Disclosed herein is a workpiece evaluating method for evaluating the gettering property of a device wafer having a plurality of devices formed on the front side of the device wafer and having a gettering layer formed inside the device wafer. The workpiece evaluating method includes the steps of applying excitation light for exciting a carrier to the device wafer, applying microwaves to a light applied area where the excitation light is applied and also to an area other than the light applied area on the device wafer, measuring the intensity of the microwaves reflected from the light applied area and from the area other than the light applied area, subtracting the intensity of the microwaves reflected from the area other than the light applied area from the intensity of the microwaves reflected from the light applied area to thereby obtain a differential signal, and determining the gettering property of the gettering layer according to the intensity of the differential signal obtained above.

(Figure 5)